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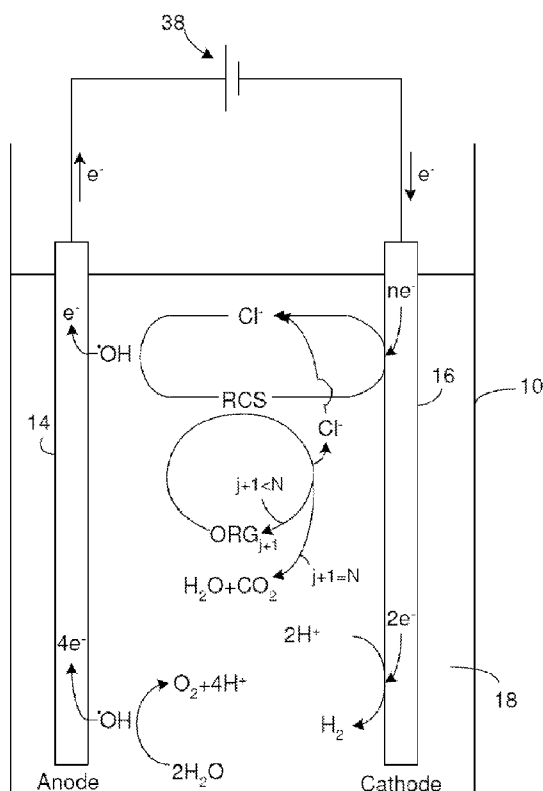
(54) **Title:** ELECTROLYSIS ELECTRODE

Figure 4

(57) **Abstract:** A water purification anode has a first semiconductor contacting a second semiconductor at a heterojunction. The second semiconductor includes TiO₂ and excludes bismuth and niobium. The first semiconductor includes iridium. In some instances, the anode includes a current collector in direct physical contact with the first semiconductor. The anode can be arranged in water such that at least one face of the second semiconductor is in direct physical contact with the water.



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ELECTROLYSIS ELECTRODE

CROSS REFERENCE TO RELATED APPLICATIONS

[0001] This Application claims the benefit of U.S. Provisional Patent Application serial number 62/023,098, filed on July 10, 2014, and incorporated herein in its entirety and this Application also claims the benefit of U.S. Provisional Patent Application serial number 62/039,729, filed on August 20, 2014, and incorporated herein in its entirety.

FIELD OF THE INVENTION

[0002] The present invention relates to electrolysis, and more particularly, to electrodes for electrolysis.

BACKGROUND

[0003] Systems are being proposed for the electrolysis of organic materials in an electrolyte. Examples of these systems include wastewater treatment systems that employ electrolysis to purify wastewater. These systems apply a potential between an anode and a cathode that are in each contact with the wastewater. The anodes in these systems often have a layer of semiconductor that contacts the wastewater. The semiconductor often includes one or more components that dissolve into the wastewater during operation of the system. Dissolution of the semiconductor components reduces the service life of the anode. Further, the ability of many of the anodes to purify water depends on the ability of the anode to generate Reactive Chlorine Species (RCS) in the water. However, these anodes generally generate reactive chlorine species at rates that are not desirable for commercialization of the technology. As a result, there is a need for improved electrolyte purification anodes.

SUMMARY

[0004] A water purification anode has a first semiconductor contacting a second semiconductor at a

heterojunction. The second semiconductor includes TiO_2 and excludes bismuth and niobium. The first semiconductor includes iridium. In some instances, the anode includes a current collector in direct physical contact with the first semiconductor.

[0005] The anode can be used in systems that purify water having organic pollutants. The anode can be arranged in the water such that at least one face of the second semiconductor is in direct physical contact with the water.

[0006] A method of operating a system for electrolysis of water includes contacting the anode with water that includes organic materials. The method also includes applying an anodic potential to the anode at a level that is sufficient to generate hydroxyl radicals bound to the surface of the anode. In some instances, the hydroxyl radicals that are bound to the surface of the anode are physisorbed to the surface of the anode.

[0007] The disclosure provides a water purification system, comprising an anode having a first semiconductor contacting a second semiconductor at a heterojunction, at least one face of the second semiconductor being in direct contact with water that includes organic materials, the second semiconductor including TiO_2 and excluding bismuth and niobium, and the first semiconductor including iridium. In one embodiment, the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta. In another embodiment, the second semiconductor excludes dopants. In yet another embodiment, the second semiconductor consists of TiO_2 . In another embodiment, the first semiconductor is in direct contact with a current collector. In another embodiment, the first semiconductor includes oxygen. In a further embodiment, the first semiconductor includes one or more stabilizing elements selected from the group consisting of Ta, Si, Sn, Ti, Sb, and Zr. In yet another embodiment, the first semiconductor

includes tantalum. In a further embodiment, the first semiconductor consists of iridium, tantalum, and oxygen. In another embodiment, the first semiconductor excludes bismuth and niobium. In a further embodiment, the first semiconductor excludes dopants. In another embodiment, hydroxyl radicals are physisorbed to the at least one face of the anode.

[0008] The disclosure also provide a water purification anode, comprising a first semiconductor contacting a second semiconductor at a heterojunction, at least one face of the second semiconductor being in direct contact with water that includes organic materials, the second semiconductor including TiO_2 and excluding bismuth, and the first semiconductor including iridium. In one embodiment, the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta. In another embodiment, the second semiconductor excludes dopants. In yet another embodiment, the second semiconductor consists of TiO_2 . In still another embodiment, the anode includes a current collector in direct contact with the first semiconductor.

[0009] The disclosure also provides a method of operating a water purification system, comprising contacting an anode with water that includes organic materials; and applying to the anode an anodic potential that is sufficient to generate hydroxyl radicals bound to the surface of the anode, the anode including a first semiconductor contacting a second semiconductor at a heterojunction, the second semiconductor including TiO_2 and excluding bismuth and niobium, and the first semiconductor including iridium. In one embodiment, the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta. In another embodiment, the second semiconductor excludes dopants.

BRIEF DESCRIPTION OF THE FIGURES

[0010] **Figure 1** illustrates an electrolysis system such as a continuous water purification system.

[0011] **Figure 2** is a perspective view of an anode.

[0012] **Figure 3** is a cross section of another embodiment of an anode.

[0013] **Figure 4** illustrates a simplified mechanism for a water purification system.

[0014] **Figure 5** is a graph comparing the long-term chemical stability of the disclosed anodes with prior anodes.

DETAILED DESCRIPTION

[0015] As used in this specification and the appended claims, the singular forms "a," "an," and "the" include plural referents unless the content clearly dictates otherwise.

[0016] Unless defined otherwise, all technical and scientific terms used herein have the same meaning as commonly understood by one of ordinary skill in the art to which the invention pertains. Although any methods and materials similar or equivalent to those described herein can be used in the practice for testing of the invention(s), specific examples of appropriate materials and methods are described herein.

[0017] Also, the use of "or" means "and/or" unless stated otherwise. Similarly, "comprise," "comprises," "comprising" "include," "includes," and "including" are interchangeable and not intended to be limiting.

[0018] It is to be further understood that where descriptions of various embodiments use the term "comprising," those skilled in the art would understand that in some specific instances, an embodiment can be alternatively described using language "consisting essentially of" or "consisting of."

[0019] All publications mentioned herein are incorporated herein by reference in full for the purpose of describing and

disclosing the methodologies, which are described in the publications, which might be used in connection with the description herein. The publications discussed above and throughout the text are provided solely for their disclosure prior to the filing date of the present application. Nothing herein is to be construed as an admission that the inventors are not entitled to antedate such disclosure by virtue of prior disclosure.

[0020] A system for purification of water having organic materials includes an anode for use in a wastewater electrolysis system. The anode includes a first semiconductor and a second semiconductor that contact one another at a heterojunction. The second semiconductor interacts with the water being purified. The second semiconductor includes, consists of, or consists essentially of TiO_2 and the first semiconductor includes oxygen and iridium. The anode has a surprisingly high rate of Reactive Chlorine Species (RCS) generation. Since many wastewater electrolysis systems use RCS to degrade organic materials, these anodes are highly suitable for use in these systems. Further, dopants introduced into the second semiconductor can be oxidized at the surface of the anode and can accordingly decrease service life of the anode. The second semiconductor can exclude dopants and/or exclude bismuth and niobium. The removal of these dopants from the second semiconductor can increase the service life of the anode and reduce the costs of the anodes. As a result, the anodes offer the possibility of extended service lives, reduced costs, and elevated RCS production rates.

[0021] Additionally, prior water purification anodes have a sealing layer between a precoat semiconductor layer and an overcoat semiconductor layer. The sealing layer was believed to improve adhesion of the overcoat to the precoat and accordingly prevented the water from coming into direct

contact with the precoat through openings in the overcoat. Direct contact between the precoat and the electrolyte was believed to allow electrical current to flow directly from the precoat through the water rather than through the overcoat as is needed for proper operation of these anodes. The inventors have found that a surprising level of performance improvement can be achieved by eliminating the sealing layer.

[0022] **Figure 1** illustrates an example of a suitable electrolysis system such as a water purification system. The system includes a vessel **10** having a reservoir. Anodes **14** and cathodes **16** are positioned in the reservoir such that anodes **14** and cathodes **16** alternate with one another. The anodes **14** and cathodes **16** are parallel or substantially parallel with one another. An electrolytic medium **18** is positioned in the reservoir such that anodes **14** and the cathodes **16** are in contact with the electrolytic medium **18**. The electrolytic medium **18** includes one or more electrolytes and can be a liquid, a solution, a suspension, or a mixture of liquids and solids. In one example, the electrolytic medium **18** is wastewater that includes organic materials and chloride (Cl^-). The chloride can be present in the electrolytic medium **18** as a result of adding a salt to the electrolytic medium **18** or the electrolytic medium **18** can include urine that is a natural source of the chloride. The electrolysis system also includes a voltage source configured to drive an electrical current through the anodes **14** and cathodes **16** so as to drive a chemical reaction in the electrolytic medium **18**.

[0023] The electrolysis system illustrated in **Figure 1** includes an inlet **20** and an outlet **22**. The electrolysis system can operate as a continuous reactor in that the electrolytic medium **18** flows into the reservoir through the inlet **20** and out of the reservoir through the outlet **22**.

Alternately, the electrolysis system can also be operated as a batch reactor. When the electrolysis system is operated as a batch reactor, the electrolytic medium **18** can be a solid, a liquid, or a combination.

[0024] **Figure 2** illustrates an anode **14** that is suitable for use in an electrolysis system. The anode **14** has faces **24** connected by one or more edges **26**. During operation of the anode **14**, at least one of the faces of the second semiconductor **32** contacts the electrolytic medium **18**. The anode **14** includes a first semiconductor **28** between a current collector **30** and a second semiconductor **32**. The first semiconductor **28** contacts the second semiconductor **32** at a heterojunction. The first semiconductor **28** contacts the current collector **30**. The second semiconductor **32** has faces **34** connected by one or more edges **36**. In some instances, at least one of the faces is in direct physical contact with the electrolytic medium. Although the current collector **30** is illustrated a sheet or foil, the current collector **30** can be a porous material such as a mesh or fabric. In some instances, the current collector **30** is embedded in the first semiconductor **28** rather than the first semiconductor **28** being a layer positioned on a face of the current collector **30**. Suitable materials for the current collector **30** include valve metals such as Ti.

[0025] The first semiconductor **28** can serve one or more functions selected from the group consisting of passivating the current collector **30**, serving as electron shuttle between the second semiconductor **32** and the current collector **30**, and decreasing the ohmic resistance of the electron transfer between the second semiconductor **32** and the current collector **30**. In some instances, direct contact between the current collector **30** and the second semiconductor **32** would result in a Schottky barrier to the transfer of electrons from the second semiconductor **32** to the current collector **30**. The

first semiconductor **28** can be selected such that the energy barrier for electron transfer from the second semiconductor **32** to the current collector **30** through the first semiconductor **28** is less than the energy barrier that would result from electron transfer from the second semiconductor **32** directly to the current collector **30**.

[0026] The second semiconductor **32** is selected such that hydroxyl radicals are formed at the surface of the second semiconductor **32** upon application of a sufficient electrical potential gradient across the interface of the second semiconductor **32** and the electrolytic medium **18**. For instance, the second semiconductor **32** can include, consists of, or consists essentially of a metal oxide such as titanium dioxide. When these metal oxides are exposed to water and a sufficient electrical gradient is applied across the interface of the anode **14** and the electrolytic medium **18** hydroxyl radicals are produced at the surface of the metal oxide. The hydroxyl radicals can be surface bound and can be represented by $\text{MO}_x(\cdot\text{OH})$ where M represents a metal element or a combination of metal elements and x is greater than or equal to one. The hydroxyl radicals are generally surface bound by physisorption but can also be chemisorbed on the surface.

[0027] The first semiconductor **28** can include, consist of, or consist essentially of a first metal oxide that includes, consists of, or consists essentially of oxygen, one or more electroactive metal elements and optionally one or more stabilizing elements. Examples of electroactive elements include, but are not limited to, Ir, Ru, Ni, Mn, and Co. Examples of stabilizing elements include, but are not limited to, Ta, Si, Sn, and Ti. Accordingly, the first semiconductor **28** can include, consist of, or consist essentially of a first metal oxide that includes, consists of, or consists essentially of oxygen, one or more electroactive metal

elements selected from the group consisting of Ir, Ru, Pt, Ni, Mn, Co, Fe, and Pb and one or more stabilizing elements selected from the group consisting of Ta, Si, Sn, Ti, Sb, and Zr. As an example, the first metal oxide can include, consist of, or consist essentially of oxygen, iridium and one or more stabilizing elements selected from the group consisting of Ta, Si, Sn, Ti, Sb, and Zr. In one example, the first metal oxide includes, consists of, or consists essentially of oxygen, iridium and tantalum. In some instances, the first metal oxide includes, consists of, or consists essentially of oxygen and one or more electroactive metal elements selected from the group consisting of Ir, Ru, Pt, Ni, Mn, Co, Fe, and Pb. In some instances, the first metal oxide includes oxygen and iridium. In one example, the first metal oxide includes oxygen, tantalum and iridium. For instance, the first metal oxide can be represented by $\text{Ir}_{0.7}\text{Ta}_{0.3}\text{O}_y$ where y is greater than 0 or 2 and/or less than 2.5 or 10.

[0028] The second semiconductor **32** can include, consist of, or consist essentially of a second metal oxide that includes, consist of, or consist essentially of oxygen and one or more elements selected from group IV. In some instances, the second semiconductor **32** includes, consists of, or consists essentially of oxygen and titanium. For instance, the second semiconductor **32** can include, consist of, or consist essentially of titanium dioxide (TiO_2).

[0029] The outermost layer of prior wastewater purification anodes have included metal oxides that are doped. Examples of dopants used with these metal oxides include, but are not limited to, dopants such as Bi, Nb, Sb, F, Cl, Mo, W, Nb, and Ta. While a semiconductor such as annealed TiO_2 is highly stable and substantially insoluble in water even at the high anodic potential needed to generate hydroxyl radicals, these dopants are often soluble in wastewater

themselves. Additionally or alternately, dopants such as bismuth are oxidized at the surface of the anode **14** during the operation of the anode **14**. This oxidation can shorten the service life of the anode **14**. Accordingly, the second semiconductors **32** disclosed above and/or the second metal oxides disclosed above can exclude dopants. In one example, the first semiconductor **28** and/or the first metal oxide excludes bismuth and niobium. In another example, the first semiconductor **28** and/or the first metal oxide excludes Bi, Nb, Sb, F, Cl, Sb, Mo, W, Nb, and Ta. In another example, the first semiconductor **28** and/or the first metal oxide excludes dopants.

[0030] Although **Figure 2** illustrates the first semiconductor **28** and the second semiconductor **32** on one side of the current collector **30**, the first semiconductor **28** and the second semiconductor **32** can be positioned on both sides of the current collector **30** as shown in the anode cross section of **Figure 3**.

[0031] In some instances, the current collector **30** is optional and the first semiconductor **28** serves as the current collector **30** for the anode **14**.

[0032] Although the second semiconductor **32** is positioned to interact directly with the electrolytic medium **18**, the anode **14** can include layers in addition to the first semiconductor **28** and the second semiconductor **32**. For instance, one or more additional layers can be positioned over the second semiconductor **32** such that the second semiconductor **32** is between the first semiconductor **28** and the one or more additional layers. In these instances, at least one of the faces of the second semiconductor **32** directly contacts the electrolytic medium **18**. For instance, the one or more additional layers can be a porous layer that allows a liquid electrolytic medium **18** to come into direct contact with a face of the second semiconductor.

[0033] **Figure 4** is a simplified illustration of the mechanism for a water purification system that makes use of advanced oxidation processes (AOP) to break organic materials into small and stable molecules such as water and CO₂. For the purposes of simplification, a single anode **14** and cathode **16** are illustrated although additional anodes **14** and/or cathodes **16** can be employed. The water purification system can be used to purify wastewater. Wastewater includes the organic materials that are normally associated with waste products and chloride that is naturally present in urine. Accordingly, wastewater can naturally operate as an electrolytic medium **18** or an electrolyte can optionally be added to the wastewater.

[0034] The details of the anode **14** construction are not illustrated; however, the second metal oxide included in the second semiconductor is labeled MO_x where M represents one or more metal elements and x is greater than 0 and is at least partially determined by the overall oxidation state of M. In some instances, M is greater than 0, 0.5, or 1 and/or less than 10 and/or a molar ratio O: M is less than 100: 1, 10: 1, 5: 1, or 2:1. When the second semiconductor includes TiO₂, M represents Ti and x represents 2.

[0035] During operation of the water purification system, an anodic potential is applied to the anode **14** at a level that is sufficient to generate surface bound hydroxyl radicals in accordance with the following reaction: $\text{MO}_x + \text{H}_2\text{O} \rightarrow \text{MO}_x(\cdot\text{OH}) + \text{H}^+ + \text{e}^-$. The hydroxyl radical generation reaction is not shown in **Figure 4**; however, the resulting hydroxyl radicals are illustrated on the surface of the anode **14**. The electrons released by the hydroxyl radical generation reaction enter the anode **14** and travel toward the voltage source **38**. The protons released by the hydroxyl radical generation reaction remain in the electrolytic medium

18 and can be transported to the cathode **16** where they are reduced so as to generate hydrogen gas.

[0036] **Figure 4** illustrates oxidation of water at the surface of the anode **14**. **Figure 4** also illustrates the chlorine cycle where chloride is oxidized at the anode surface so as to generate Reactive Chlorine Species (RCS). The reactive chlorine species are reduced at the cathode surface to generate chloride. Reactive chlorine species are free chlorine plus chlorine radicals. Examples of free chlorine include, but are not limited to, Cl_2 , HOCl , and ClO^- . Examples of chlorine radicals include, but are not limited to, $\text{Cl}\cdot$ and the radical ion $\text{Cl}_2^{\cdot-}$.

[0037] In one example of the chlorine cycle, chloride reacts with a hydroxyl radical at the anode surface so as to generate HOCl in the electrolytic medium **18** and MO_x at the anode surface. The HOCl is an acid (hypochlorous acid) that accordingly partially dissociates into a proton (H^+) and hypochlorite (ClO^-) in the electrolytic medium **18**. Hypochlorite and water can react at the surface of the cathode **16** to generate a chloride and a hydroxyl ion that each receives an electron from the cathode **16**. In another part of the chlorine cycle, the chloride is oxidized at the anode surface to generate an atomic chlorine radical ($\text{Cl}\cdot$) in the electrolytic medium **18**. The atomic chlorine radical can interact with chloride to form the radical ion $\text{Cl}_2^{\cdot-}$. The radical ion $\text{Cl}_2^{\cdot-}$ can be reduced at the cathode surface to generate two chlorides in the electrolytic medium **18**. The hypochlorous acid, hypochlorite, atomic chlorine radical, and radical ion $\text{Cl}_2^{\cdot-}$ serve as Reactive Chlorine Species (RCS).

[0038] **Figure 4** also illustrates the organic species degradation cycle in the electrolyte. The organic material goes through a series of reactions that can convert the organic material into multiple fragments. The reactions continue for N reaction cycles until the fragments are all

converted into small and stable molecules such as H_2O and CO_2 . In **Figure 4**, the variable j represents the number of reaction cycles that an organic compound (ORG) has experienced. Accordingly, ORG_0 represents the organic compound before the organic compound has reacted with the RCS and ORG_1 represents the one or more fragments of the organic compound that remain after the first reaction with the RCS. As is illustrated, each of the $N-1$ reaction cycle reacts ORG_j with one or more RCS and generates one or more chlorides in the electrolytic medium **18**. The N th reaction cycle reacts ORG_{N-1} with one or more RCS to generate small stable molecules such as H_2O and CO_2 . In some instances, the small stable molecules such as H_2O and CO_2 are also generated earlier in the reaction cycle. In one example, during each reaction cycle, at least one radical ion $\text{Cl}_2^{\cdot-}$ reacts with ORG_j and generates ORG_{j+1} and one or more chlorides in the electrolytic medium **18**.

[0039] Although the system of **Figure 4** illustrates degrading of organic materials through reactions between the organic materials and the RCS, the organic materials can also be degraded through direct oxidation of the organic materials or organic material fragments at the surface of the anode **14**. This direct mechanism can be in addition to the reaction with RCS or an alternative to the RCS reactions.

EXAMPLES

Example 1

[0040] A first anode was prepared. A Ti metal sheet ($3 \times 2 \text{ cm}^2$, 0.5 mm thickness) served as the substrate. The substrate was pretreated by sequentially sandblasting, degreasing with 50 V/V% acetone, and etching in boiling 10 M/V% oxalic acid right before fabrication. A layer of $\text{Ir}_{0.7}\text{Ta}_{0.3}\text{O}_y$ served as the first semiconductor. The $\text{Ir}_{0.7}\text{Ta}_{0.3}\text{O}_y$ was formed on the substrate by sequentially forming several sub-layers of the $\text{Ir}_{0.7}\text{Ta}_{0.3}\text{O}_y$. Each sub-layer was prepared by brushing precursor (70 mM H_2IrCl_6 + 30 mM TaCl_5 in 1:1 ethanol and isopropanol) on both sides of

the substrate, drying the result at 80 °C (10 min) and annealing at 525 °C for 10 min. This same technique was repeated so as to form five additional sub-layers. The result was further heat treated at 525 °C for 1 hour as a final annealing. The result had the first semiconductor loading of 0.64 mg cm⁻² average over the surface of the current collector.

[0041] A layer of TiO₂ served as the second semiconductor. The layer of TiO₂ was formed by sequentially forming several sub-layers of TiO₂ on top of one another. The first sub-layer of TiO₂ was formed by brushing a precursor solution (250 mM TiOSO₄ and 312.5 mM H₂SO₄ in 1:1V ethanol+water solution) onto the first semiconductor on both sides of the substrate. The result was dried at 80 °C for 10 min and then annealed at 425 °C for 10 min. This same technique was repeated so as to form seven additional sub-layers such that each additional sub-layer was formed on the previously formed sub-layer. The result was further annealed at 425 °C for 1 hour and the result served as a first anode.

Example 2

[0042] A second anode was prepared. The substrate and first semiconductor were prepared as disclosed in Example 1. A layer of TiO₂ served as the second semiconductor. The layer of TiO₂ was formed by sequentially forming several sub-layers of TiO₂ on top of one another. The first sub-layer of TiO₂ was formed by brushing a precursor solution (250 mM TiOSO₄ with 0.5 M glycolic acid in 1:1V isopropanol and water solution) onto the first semiconductor on both sides of the substrate. The result was dried at 80 °C for 10 minutes and then annealed at 425 °C for 10 minutes. This same technique was repeated so as to form seven additional sub-layers such that each additional sub-layer was formed on the previously formed sub-layer. The result was further annealed at 425 °C for 1 hour and the result served as a second anode.

Example 3

[0043] A third anode was prepared. The substrate and first semiconductor were prepared as disclosed in Example 1. A layer of TiO_2 served as the second semiconductor. The layer of TiO_2 was formed by sequentially forming several sub-layers of TiO_2 on top of one another. A precursor for the first sub-layer of TiO_2 was formed by dissolving 1.6 M TiOSO_4 in 2 M H_2SO_4 and neutralizing the result by adding 50% KOH. The resulting precipitates were harvested by centrifugation and glycolic acid was added (Ti:glycolic acid = 1:1). The mixture was stirred at 75 °C for 2- 3 days to achieve a complete dissolution. The resulting solution was diluted to have a final Ti concentration of 250 mM. The resulting precursor solution was brushed onto the first semiconductor on both sides of the substrate. The result was dried at 80 °C for 10 min and then annealed at 425 °C for 10 minutes. This same technique was repeated so as to form seven additional sub-layers such that each additional sub-layer was formed on the previously formed sub-layer. The result was further annealed at 425 °C for 1 hour and the result served as a third anode.

Example 4

[0044] A fourth anode was prepared. The substrate and first semiconductor were prepared as disclosed in Example 1. A layer of TiO_2 served as the second semiconductor. The layer of TiO_2 was formed by sequentially forming several sub-layers of TiO_2 on top of one another. The precursor for the first sub-layer of TiO_2 was formed by adding titanium butoxide (250 mM of final concentration) and glycolic acid (375 mM) into a relevant amount of water. The resulting precipitates were re-dissolved with 30 W/W% H_2O_2 (ca. 40% of final precursor volume). Exothermic reactions with a presence of dark red color appeared with vigorous generations of CO_2 and O_2 bubbles. In order to adjust the pH to be circum-neutral, small aliquot of concentrated NH_4OH (ca. 3.5% of final precursor volume) was added. The color quickly changed into yellow with the pH adjustment while mild bubble generations (including N_2)

continued with a decay of residual H₂O₂. The resulting precursor solution was brushed onto the first semiconductor on both sides of the substrate. The result was dried at 80 °C for 10 min and then annealed at 425 °C for 10 min. This same technique was repeated so as to form seven additional sub-layers such that each additional sub-layer was formed on the previously formed sub-layer. The result was further annealed at 425 °C for 1 hour and the result served as the second anode.

Example 5

[0045] A first comparative anode was generated having only the first semiconductor on the substrate. The substrate and first semiconductor were prepared as disclosed in Example 1.

Example 6

[0046] A second comparative anode was generated with a structure that is known for use in wastewater electrolysis. The anode has multiple layers on a substrate. In particular, the anode has a precoat on the substrate, a sealcoat on the precoat, a slurry coat on the sealcoat, and an overcoat on the slurry coat. The overcoat is the outermost layer of the anode and contacts the electrolyte during operation of the system.

[0047] A Ti metal sheet (3 × 2 cm², 0.5 mm thickness) served as the substrate. The precoat was IrO₂/Ta₂O₅ at a Ir:Ta molar ratio of 67:33. The seal coat was SnO₂/Bi₂O₃ at a Sn:Bi molar ratio of 90:10. The slurry coat was Bi doped TiO₂ at a Ti:Bi molar ratio of 96:4. The overcoat was TiO₂/Bi₂O₃ at a Ti:Bi molar ratio of 70:30.

Example 7

[0048] The performance of the anodes was tested using a system such as the system disclosed in the context of Figure 1. The system included a stainless steel cathode (3×2 cm², 5 mm

distance) in parallel with one of the anodes from examples 1 through 5. The system also included a Ag/AgCl/Sat. KCl reference electrode (Basi Inc.). The electrolyte was a 50 mM NaCl solution. These components were arranged in a reservoir having a working volume of about 60 mL with a Vycor® glass tip of the reference electrode being 3 mm apart from the center of the anode.

[0049] An anodic potential (E_a) was applied between the anode and cathode so as to perform potentiostatic electrolysis. The potential was applied from a potentiostat (SP-50, BioLogic). The anodic potential was converted to the normal hydrogen electrode (NHE) scale by $E_a(\text{NHE}) = E_a(\text{Ag/AgCl}) + 0.197 \text{ V}$. The rate and current efficiency of Reactive Chlorine Species (RCS) generation were estimated at different E_a ; 2.0, 2.5, and 3.0 V. The RCS concentration was measured by DPD (N,N-diethyl-p-phenylenediamine) reagent at a fixed time interval (2 minutes) for three times with proper dilutions. The current efficiency for the RCS generation was estimated by $\eta_{\text{RCS}} = 2VFd[\text{Cl}_{\text{DPD}}]/Idt$ where V is electrolyte volume (0.06 L), F is Faraday constant ($96485.3 \text{ C mol}^{-1}$), $[\text{Cl}_{\text{DPD}}]$ is the concentration of RCS (M), I is current (A), and t is electrolysis time (sec). The results of these tests are presented in the following Table 1.

[0050] TABLE 1:

	Anodic Potential (V NHE)	First Comparative Anode	Second Comparative Anode	First Anode	Second Anode	Third Anode	Fourth Anode
Current Density (A/m^2)	2.0	188	122	151	145	146	141
	2.5	356	293	291	309	263	258
	3.0	530	450	441	427	421	425
Current Efficiency (%)	2.0	53.0	25.7	69.6	82.8	81.7	84.7
	2.5	52.2	29.3	70.7	75.5	82.2	86.1
	3.0	53.8	29.9	72.5	83.2	71.1	84.0

Reactive Chlorine Evolution Rate (mmol/m ² s)	2.0	0.516	0.137	0.546	0.616	0.616	0.618
	2.5	0.963	0.402	1.07	1.19	1.12	1.15
	3.0	1.60	0.586	1.74	1.86	1.55	1.84

[0051] For a given Anodic Potential, Table 1 shows differences between the results achieved for the first through fourth anodes. These differences are believed to be a result of the anodes having different second semiconductor surface areas that result from differences in the compositions of the precursors used to generate the anodes.

[0052] Table 1 shows that the current density for the first comparative anode is higher than the current density measured for each of the other anodes. This result is believed to be a result of the electrical resistance across the one or more hetero-junctions that are present in each of the other anodes but not presenting the first comparative electrode. The current density for the first through fourth anodes are comparable with the current density through the second comparative anode. However, the current efficiency achieved by the first through fourth anodes are surprisingly (~30-60%) higher than the current efficiency achieved by the first comparative anode and about 2 to 3 times higher than the current efficiency achieved by the second comparative anode. Further, the rate of RCS generation was generally higher for the first through fourth anodes that was achieved with the first comparative electrode and was surprisingly higher (~2.5-4 times) than the rate achieved with the second comparative anode.

Example 8

[0053] The mechanical and chemical stability of the second comparative anode and the first through fourth anodes were tested. The second semiconductor on the first anode and the second anode were not mechanically stable and flaked off from mechanical stress (scratching). This is believed to be a result

of the precursors for the first anode and the second anode being close to a suspension rather than a complete solution. In contrast, the second semiconductor included in the third anode and the fourth anode was prepared from aqueous Ti solutions and the resulting TiO_2 was more mechanically stable.

[0054] The chemical stability of the second comparative anode and the first through fourth anodes were tested using accelerated life tests. Cells were generated such that each cell included one of the anodes aligned with a stainless steel cathode ($0.5 \times 2 \text{ cm}^2$) at a distance of 3 mm in a 1 M NaClO_4 solution (electrolytic medium) in conical tubes. A Neware Battery Testing System powered a galvanostatic electrolysis in each cell at a current density of 1 A/cm^2 . The electrolytic medium was replaced in 3 to 5 hour intervals and dissociated amounts of Ti, Bi, and Ir in the electrolyte were quantified by Agilent inductivity coupled plasma-mass spectrometry (ICP-MS). Figure 5 is a plot of the level of dissolved Ti versus electrolysis time for the second comparative anode, the third anode, and the fourth anode.

[0055] **Figure 5** shows that the second comparative anode showed much faster dissolution of the Ti than was shown by either the third anode or the fourth anode. The rapid dissolution of the Ti in the second comparative anode is believed to be a result of the oxidation of the Bi on the surface of the anode. The third anode did illustrate a higher Ti dissolution rate than the fourth anode. It is believed that the additional stability achieved by the fourth anode may be a result of the third anode having a reduced level of crystallinity in the second semiconductor. A comparison of the results shown in Table 1 with **Figure 5** indicates that the fourth anode provided the highest level of RCS generation, mechanical stability, and chemical stability.

[0056] Other embodiments, combinations and modifications of this invention will occur readily to those of ordinary

skill in the art in view of these teachings. Therefore, this invention is to be limited only by the following claims, which include all such embodiments and modifications when viewed in conjunction with the above specification and accompanying drawings.

CLAIMS

1. A water purification system, comprising:
an anode having a first semiconductor contacting a second semiconductor at a heterojunction,
at least one face of the second semiconductor being in direct contact with water that includes organic materials,
the second semiconductor including TiO_2 and excluding bismuth and niobium, and
the first semiconductor including iridium.
2. The system of claim 1, wherein the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta.
3. The system of claim 1, wherein the second semiconductor excludes dopants.
4. The system of claim 1, wherein the second semiconductor consists of TiO_2 .
5. The system of claim 1, wherein the first semiconductor is in direct contact with a current collector.
6. The system of claim 1, wherein the first semiconductor includes oxygen.
7. The system of claim 6, wherein the first semiconductor includes one or more stabilizing elements selected from the group consisting of Ta, Si, Sn, Ti, Sb, and Zr.
8. The system of claim 6, wherein the first semiconductor includes tantalum.

9. The system of claim 8, wherein the first semiconductor consists of iridium, tantalum, and oxygen.
10. The system of claim 1, wherein the first semiconductor excludes bismuth and niobium.
11. The system of claim 10, wherein the first semiconductor excludes dopants.
12. The system of claim 1, wherein hydroxyl radicals are physisorbed to the at least one face of the anode.
13. A water purification anode, comprising:
a first semiconductor contacting a second semiconductor at a heterojunction,
at least one face of the second semiconductor being in direct contact with water that includes organic materials,
the second semiconductor including TiO_2 and excluding bismuth, and
the first semiconductor including iridium.
14. The anode of claim 13, wherein the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta.
15. The anode of claim 13, wherein the second semiconductor excludes dopants.
16. The anode of claim 13, wherein the second semiconductor consists of TiO_2 .
17. The anode of claim 13, wherein the anode includes a current collector in direct contact with the first semiconductor.

18. A method of operating a water purification system, comprising:
- contacting an anode with water that includes organic materials; and
 - applying to the anode an anodic potential that is sufficient to generate hydroxyl radicals bound to the surface of the anode,
 - the anode including a first semiconductor
 - contacting a second semiconductor at a heterojunction,
 - the second semiconductor including TiO_2 and excluding bismuth and niobium, and
 - the first semiconductor including iridium.
19. The method of claim 18, wherein the second semiconductor excludes Sb, F, Cl, Sb, Mo, W, Nb, and Ta.
20. The method of claim 18, wherein the second semiconductor excludes dopants.

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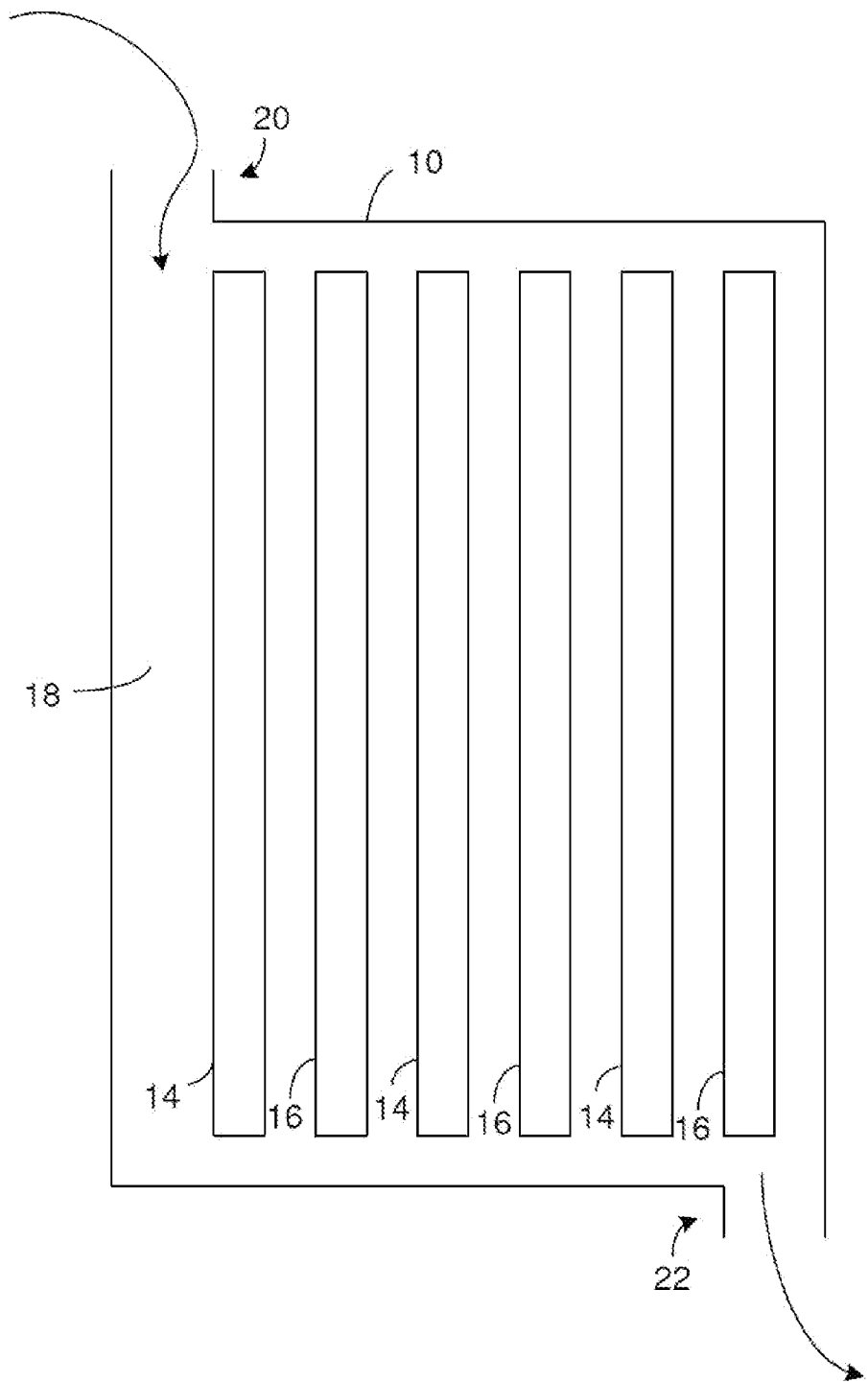


Figure 1

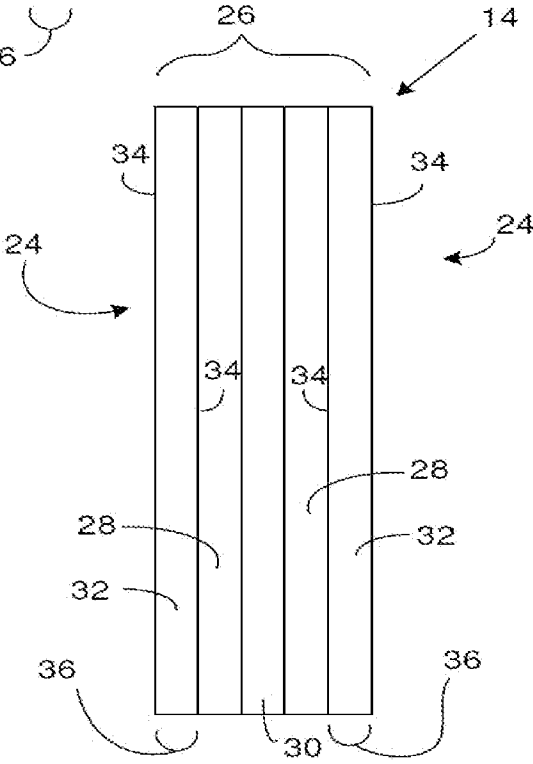
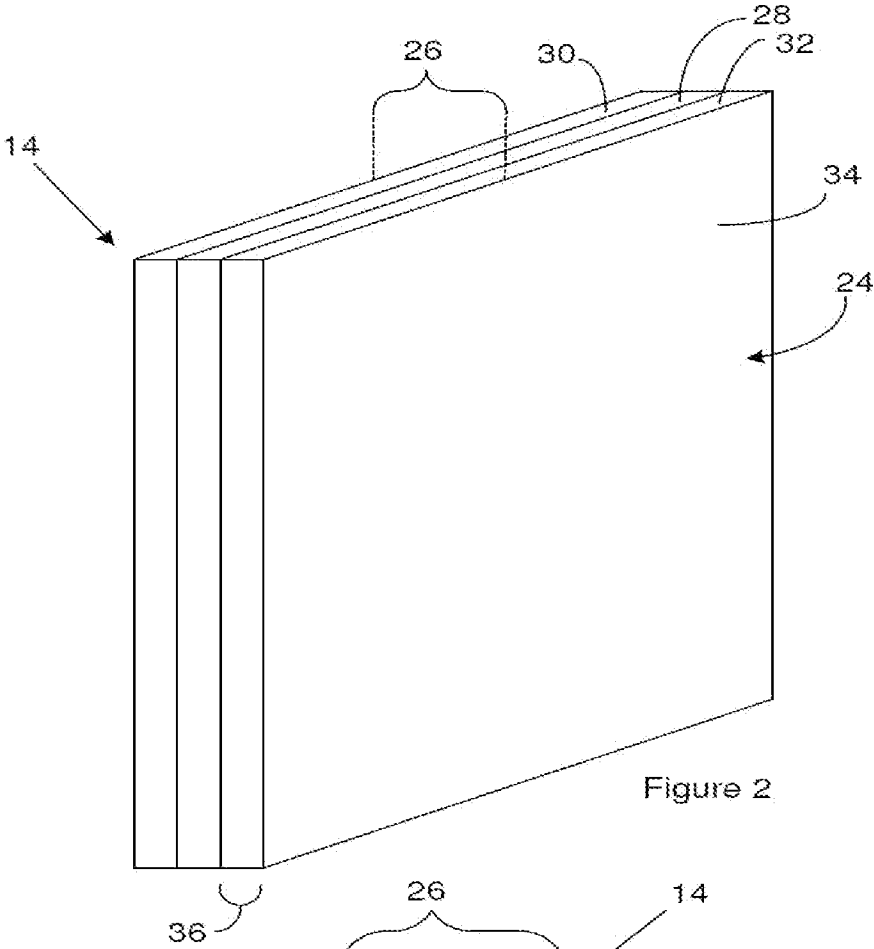


Figure 3

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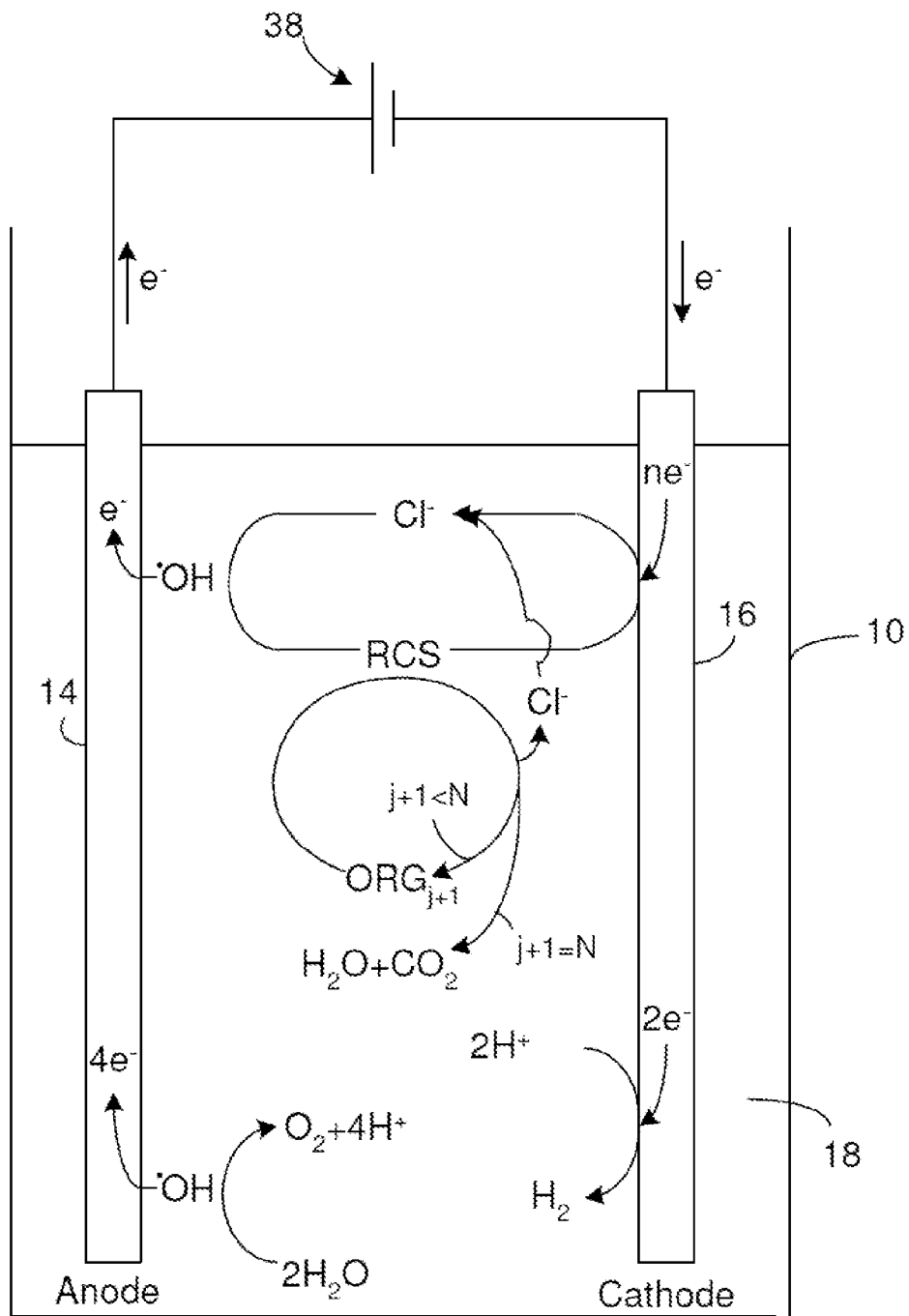


Figure 4

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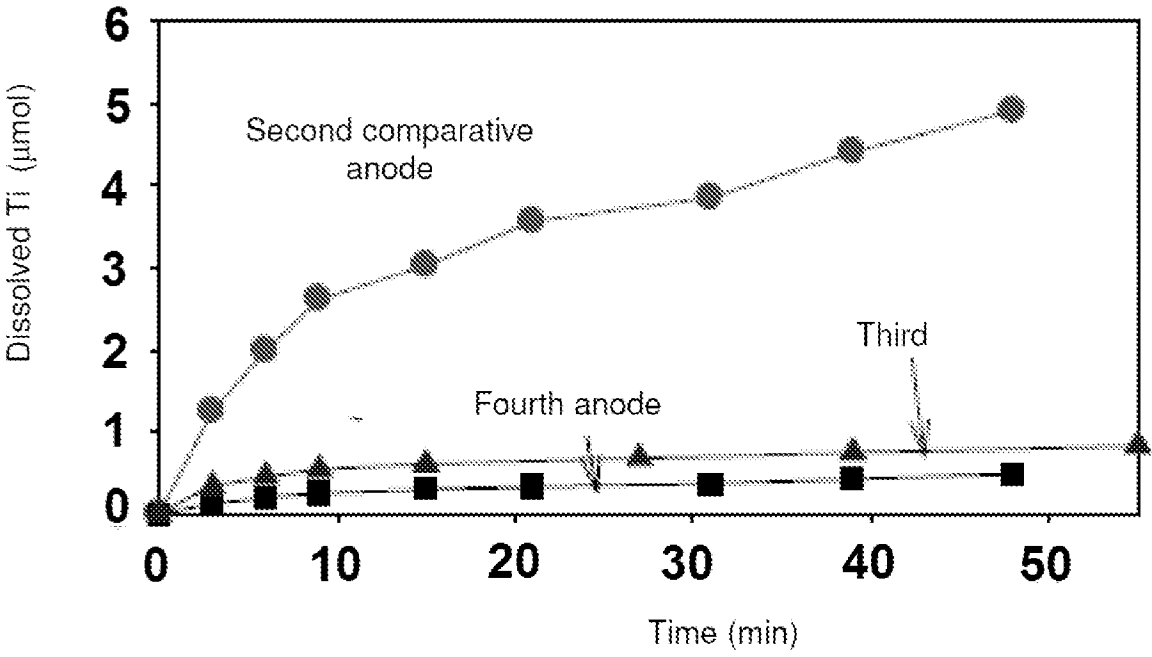


Figure 5

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US2015/013193**A. CLASSIFICATION OF SUBJECT MATTER****C02F 1/46(2006.01)i, C02F 1/461(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

C02F 1/46; C25B 11/03; B05D 5/12; C25B 11/04; C25D 3/38; C25B 15/02; C25B 11/00; C02F 1/461; C25B 13/04; C25B 11/06

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & keywords: electrolysis, electrode, anode, dissolution, water purification, sealing, overcoat, precoat

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
X	US 2012-0279872 A1 (CHEN, A. et al.) 08 November 2012 See abstract; paragraphs [0043]-[0083]; figures 1(A)-4.	1-20
A	US 2001-0042682 A1 (WERES, O. et al.) 22 November 2001 See abstract; paragraphs [0032]-[0039]; figures 1-5.	1-20
A	US 2007-0000774 A1 (WERES, OLEH) 04 January 2007 See abstract; paragraphs [0034]-[0048]; figure 1.	1-20
A	US 6527939 B1 (HARDEE, KENNETH L.) 04 March 2003 See abstract; column 2, line 44-column 5, line 51.	1-20
A	US 2012-0090988 A1 (Li, J. et al.) 19 April 2012 See abstract; claims 1-6.	1-20



Further documents are listed in the continuation of Box C.



See patent family annex.

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"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

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"&" document member of the same patent family

Date of the actual completion of the international search

30 April 2015 (30.04.2015)

Date of mailing of the international search report

07 May 2015 (07.05.2015)

Name and mailing address of the ISA/KR

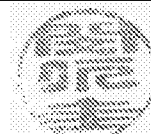
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INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2015/013193

Patent document cited in search report	Publication date	Patent family member(s)	Publication date
US 2012-0279872 A1	08/11/2012	WO 2010-132993 A1	25/11/2010
US 2001-0042682 A1	22/11/2001	US 2004-0003993 A1	08/01/2004
		US 6589405 B2	08/07/2003
		US 7077937 B2	18/07/2006
		WO 01-87776 A2	22/11/2001
		WO 01-87776 A3	28/03/2002
US 2007-0000774 A1	04/01/2007	US 7494583 B2	24/02/2009
US 6527939 B1	04/03/2003	EP 1552041 A2	13/07/2005
		JP 2003-503598 A	28/01/2003
		JP 2006-503187 A	26/01/2006
		KR 10-2005-0083767 A	26/08/2005
		US 2004-0031692 A1	19/02/2004
		US 7247229 B2	24/07/2007
		WO 2001-000905 A1	04/01/2001
		WO 2004-038071 A2	06/05/2004
		WO 2004-038071 A3	20/01/2005
US 2012-0090988 A1	19/04/2012	EP 2436437 A1	04/04/2012
		JP 2012-527354 A	08/11/2012
		WO 2010-135886 A1	02/12/2010